SOT-23 Plastic-Encapsulate Transistors Formosa MS

MMBT3904 TRANSISTOR (NPN)

FEATURES

- As complementary type, the PNP transistor MMBT3906 is Recommended
- Epitaxial planar die construction

MARKING:1AM

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	60	V	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	6	V	
Ic	Collector Current -Continuous	0.2	Α	
Pc	Collector Power Dissipation	0.2	W	
TJ	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature	-55-150	°C	

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA,I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA,I _C =0	6			٧
Collector cut-off current	I _{CBO}	V _{CB} = 60 V , I _E =0			0.1	μΑ
Collector cut-off current	I _{CEO}	V _{CE} =30V, V _{BE(off)} =3V			50	nA
Emitter cut-off current	I _{EBO}	V_{EB} = 5V , I_{C} =0			0.1	μΑ
	h _{FE(1)}	V _{CE} =1V,I _C =10mA	100		400	
	h _{FE(2)}	V _{CE} =1V,I _C =50mA	60			
DC current gain	h _{FE(3)}	V _{CE} =1V,I _C =100mA	30			
	V _{CE(sat)}	I _C =50mA,I _B =5mA			0.3	V
	V _{BE(sat)}	I _C =50mA,I _B =5mA			0.95	V
Transition frequency	f _T	V _{CE} =20V,I _C =10mA,f=100MHz	250			MHz
Delay time	t _d	V _{CC} =3V,V _{BE} =-0.5V,I _C =10mA ,			35	nS
Rise time	t _r	I _{B1} =-I _{B2} = 1mA			35	nS
Storage time	ts	V _{CC} =3V,I _C =10mA , I _{B1} =-I _{B2} = 1mA			200	nS
Fall time	t _f				50	nS

CLASSIFICATION OF h_{FE1}

Rank	0	Υ	G
Range	100-200	200-300	300-400

Typical Characteristics

MMBT3904











